

**AMENDMENTS TO THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**LISTING OF CLAIMS:**

Claim 1 (original): A transistor comprising:  
a source electrode and a drain electrode arranged in mutually opposing relation;  
a semiconductor film comprising at least one layer disposed between the source electrode and the drain electrode;  
a gate electrode disposed in adjacent relation to the semiconductor film; and  
a gate insulating film disposed between the gate electrode and each of the source electrode, the drain electrode, and the semiconductor film, wherein  
a concentration of fluorine contained in the gate insulating film is  $1 \times 10^{20}$  atoms/cm<sup>3</sup> or less.

Claim 2 (original): The transistor of claim 1, wherein the concentration of the contained fluorine is  $1 \times 10^{19}$  atoms/cm<sup>3</sup> or less.

Claim 3 (original): The transistor of claim 1, which is of a field-effect type.

Claim 4 (original): The transistor of claim 1, wherein the gate insulating film is an amorphous silicon nitride film.

Claim 5 (original): The transistor of claim 1, wherein the gate insulating film is deposited by a CVD method.

Claim 6 (original): A CVD apparatus used to deposit the gate insulating film in the transistor of claim 1, the CVD apparatus comprising:  
an electrode having a plurality of gas supply holes and disposed in a reaction chamber, wherein

a surface of the electrode is composed of a non-porous layer.

Claim 7 (original): A transistor comprising the gate insulating film deposited by using the CVD apparatus of claim 6.

Claim 8 (currently amended): A liquid crystal display device comprising the transistor of ~~any one of claims 1, 2, 3, 4, 5, and 7~~ as a switching element for a pixel electrode portion.